Physics FSC Part 2 Chapter 18 Online MCQ's Test

Sr	Questions	Answers Choice
1	The potential difference across the depletion region of germanium is.	A. 0.3 V B. 0.5 V C. 0.7 V D. 0.8 V
2	The potential difference across depletion region in case of Si is	A. 0.6 volt B. 0.9 volt C. 0.7 volt D. 0.2 volt
3	Improper bisting of a transistor circiut produces:	A. Heavy loading of emitter current B. Distortion in the output output signal C. Excessive heat at collector terminal D. Faculty location of load line
4	Which is not fundamental logic gate.	A. NOT B. AND C. OR D. NAND
5	A light emitting diode emits light only when	A. Reverse biased B. Forward biased C. Unbiased D. None of these
6	In a transistor, collector current is controlled by:	A. Collector voltage B. Base current C. Collector resistance D. All of the above
7	Which factor does not affect the conductivity of PN-Junction diode.	A. Doping B. Temperature C. Voltage D. Pressure
8	The ratio Beta in transistor is called.	A. Voltage gain B. Emitter gain C. Current gain D. Nuclear gain
9	Transistor was discovered by	A. Young B. Curie C. John Bardeen D. Shale's
10	The average gap for Germanium at 0K is	A. 1.12 ev B. 0.02 ev C. 6.72 ev D. 7.2 ev
11	For rectification we use.	A. Transformer B. Diode C. Choke D. Generator
12	OR gate is represented by:	A. X = A+B B. X=A.B C. X=A+B D. X=A.B
13	In case of reverse biasing, current is flown due to:	A. Minority charge carriers B. Majority charge carriers C. Electrons D. Protons
14	In full wave rectification number of diodes required are equal to.	A. 2 B. 3 C. 4 D. 5
15	Photo diode is used for detection of.	A. Heat B. Magnet C. Current

		D. Light
16	The potential barrier for silicon is.	A. 0.7 V B. 0.5 V C. 0.3 V D. 0.9 V
17	In photovoltaic cell, current is directly proportional to.	A. Wavelength of light B. Intensity of light C. Energy D. Frequency of light
18	Logic gate can control some physical parameters like.	A. Temperature, Pressure B. Resistance, Inductance C. Capacitance, Impedance D. Current, voltage
19	Doping is made comparatively larger in	A. Emitter B. Base C. Collector D. P -type semi conductor
20	The P.D develop in case of silicon is:	A. 0.7V B. 0.3V C. 0.5V D. 0.9V